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查询"2SK3843"协函函 Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIII)

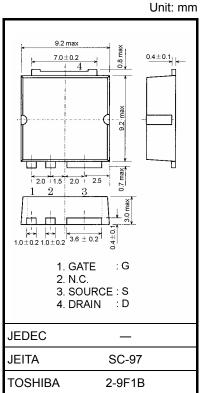
2SK3843

Switching Regulator, DC/DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: RDS (ON) = 2.7 m\Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 120 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- Enhancement mode $: V_{th} = 1.5 \sim 3.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$ •

Maximum Ratings (Ta = 25°C)

Character	stic	Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	40	V
Drain–gate voltage (R_{GS} = 20 k Ω)		V _{DGR}	40	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC (Note 1)	Ι _D	75	А
	Pulse (Note 1)	I _{DP}	300	А
Drain power dissipation	n (Tc = 25°C)	PD	125	W
Single-pulse avalanche energy (Note 2)		E _{AS}	542	mJ
Avalanche current		I _{AR}	75	А
Repetitive avalanche e	energy (Note 3)	E _{AR}	12.5	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature ra	ange	T _{stg}	-55~150	°C



Weight: 0.74 g (typ.)

Thermal Characteristics

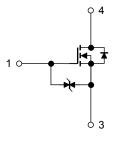
Characteristic	Symbol	Мах	Unit	
Thermal resistance, channel to case	R _{th (ch–c)}	1.0	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 100 µH, I_{AR} = 75 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature.

This transistor is an electrostatic-sensitive device. Handle with care.



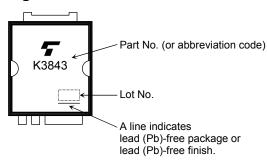
Etectrica Perfaracter istics (Ta = 25°C)

Chara	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	_	±10	μA
Drain cutoff curr	ent	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	_	—	10	μA
Drain-source breakdown voltage		V _(BR) DSS	I _D = 10 mA, V _{GS} = 0 V	40	—		v
		V (BR) DSX	$I_{\rm D}$ = 10 mA, $V_{\rm GS}$ = -20 V	15	—		
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	—	3.0	V
Drain-source ON resistance		Pro (out)	V _{GS} = 4.5 V, I _D = 38 A	_	4.3	8.0	mΩ
		R _{DS (ON)}	V _{GS} = 10 V, I _D = 38 A	_	2.7	3.5	
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 38 A	60	120		S
Input capacitance	put capacitance C _{iss}				11200		pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	800		
Output capacitance		Coss			1350		
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0}V \int I_{D} = 38 \text{ A}$	_	12	_	
	Turn–on time	t _{on}		_	40	_	
	Fall time	t _f		_	65	_	ns
	Turn–off time	t _{off}	ν _{DD} ≃ 20 v Duty ≦ 1%, t _w = 10 μs	_	260	_	
Total gate charge (gate–source plus gate–drain)		Qg	V _{DD} ≈ 32 V, V _{GS} = 10 V, I _D = 75 A	_	210	_	nC
Gate-source charge		Q _{gs}		—	150	—	
Gate-drain ("Miller") Charge		Q _{gd}		_	60	—	

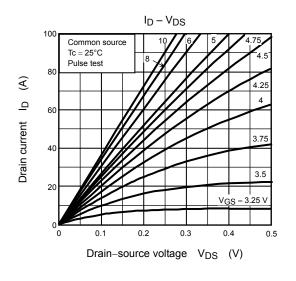
Source–Drain Ratings and Characteristics (Ta = 25°C)

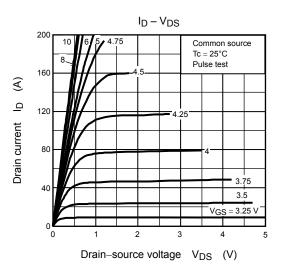
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	75	А
Pulse drain reverse current (Note 1)	I _{DRP}	_			300	А
Forward voltage (diode)	V _{DSF}	I _{DR1} = 75 A, V _{GS} = 0 V	_	_	-1.5	V
Reverse recovery time	t _{rr}	I _{DR} = 75 A, V _{GS} = 0 V		100		ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 30 A/µs	_	120	_	nC

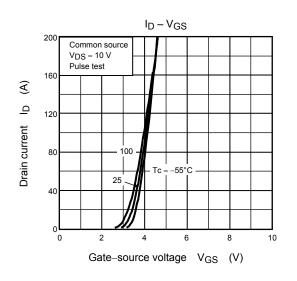
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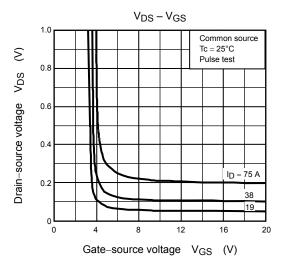


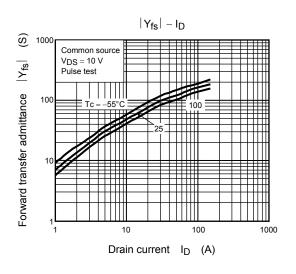
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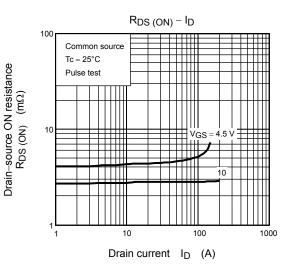




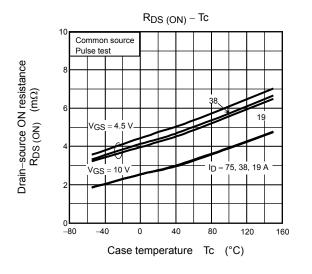


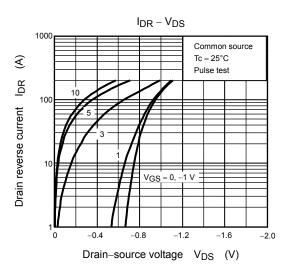


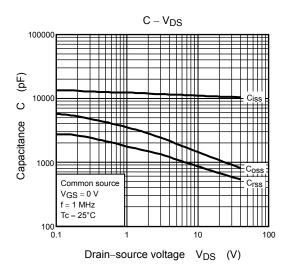


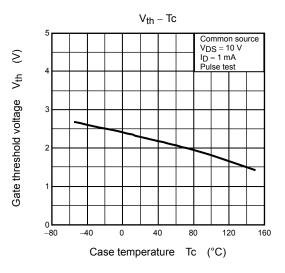


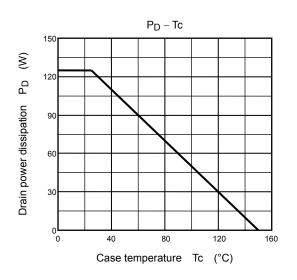
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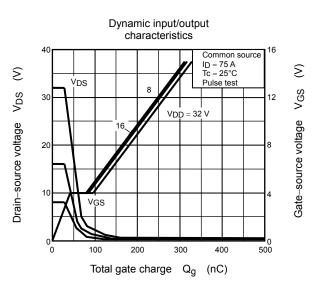




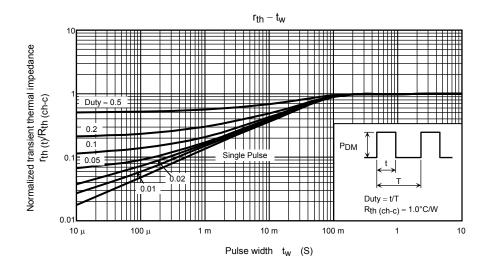


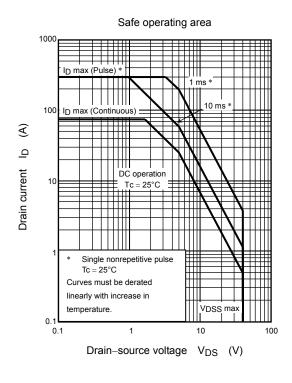


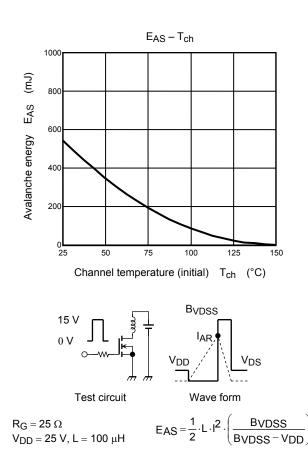




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